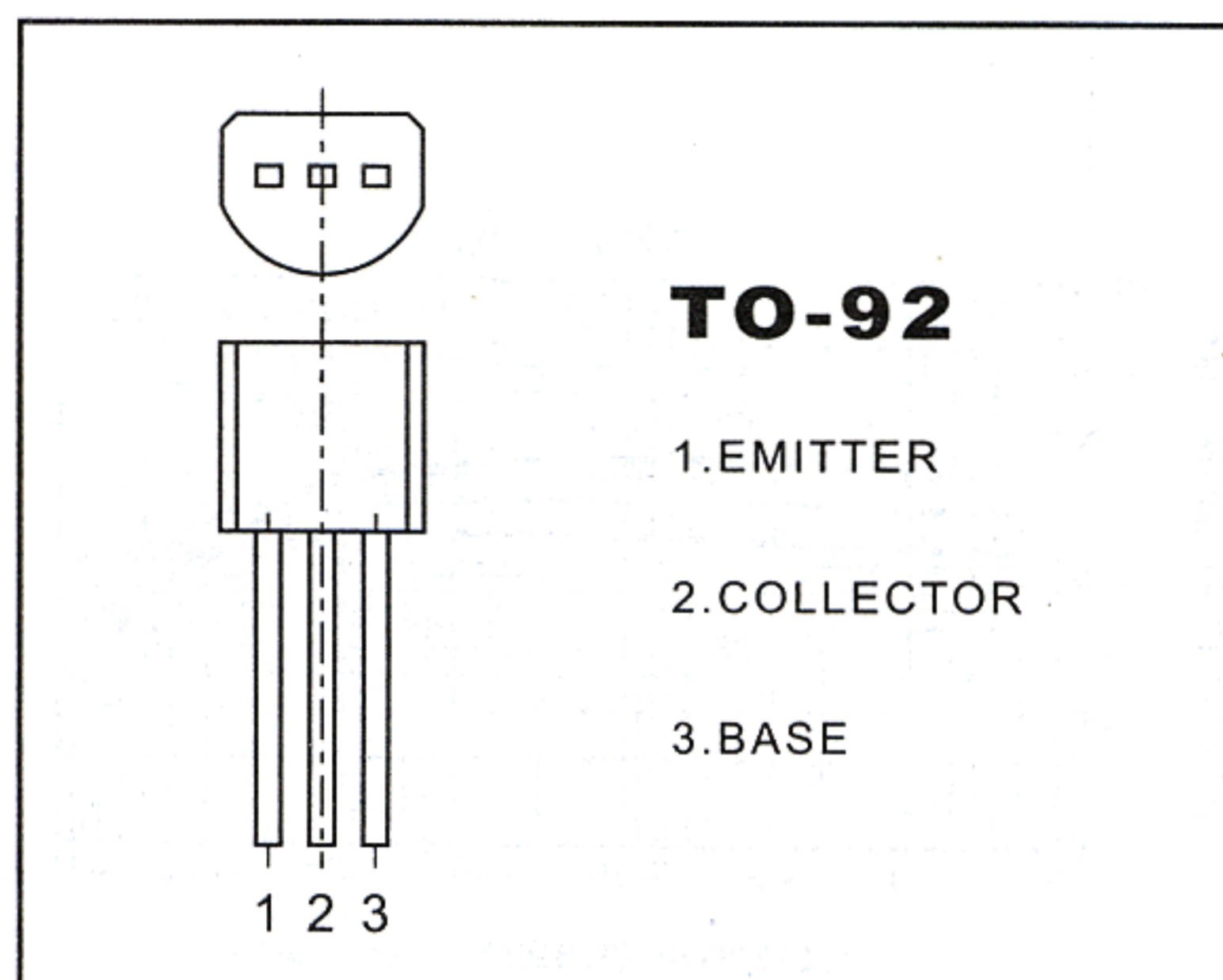


2SA562 TRANSISTOR(NPN)



FEATURES

Power dissipation

P_{CM} : 0.5W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -35 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100 \mu A, I_E = 0$	-35		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1mA, I_B = 0$	-30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100 \mu A, I_C = 0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB} = -35 V, I_E = 0$		-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5 V, I_C = 0$		-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -1 V, I_C = -100 mA$	70	240	
	$h_{FE(2)}$	$V_{CE} = -6 V, I_C = -400 mA$	25		
Collector-emitter saturation voltage	V_{CEsat}	$I_C = -100 mA, I_B = -10 mA$		-0.25	V
Base-emitter voltage	V_{BE}	$V_{CE} = -1 V, I_C = -100 mA$		-1	V
Transition frequency	f_T	$V_{CE} = -6 V, I_C = -20 mA$	200		MHz
		$f = 30MHz$			

CLASSIFICATION OF $h_{FE(1)}$

Rank		O	Y
Range	$h_{FE(1)}$	70-140	120-240
	$h_{FE(2)}$	25min	40min

